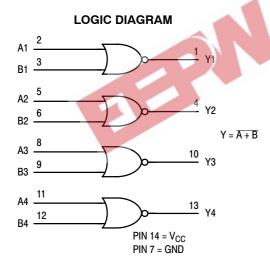
# **Quad 2-Input NOR Gate**

# **High-Performance Silicon-Gate CMOS**

The MC74HC02A is identical in pinout to the LS02. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7.0 A
- Chip Complexity: 40 FETs or 10 Equivalent Gates
- Pb-Free Packages are Available



# **PIN ASSIGNMENT**

Y1 [	1 ●		v <sub>cc</sub>
A1 [	2	13	] Y4
B1 [	3	12	] B4
Y2 [	4	11	] A4
A2 [	5	10	] Y3
B2 [	6	9	] B3
GND [	7	8	_ A3
			l



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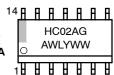
# MARKING DIAGRAMS



PDIP-14 N SUFFIX CASE 646



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

# **FUNCTION TABLE**

Inp	Inputs	
Α	В	Υ
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	±[ <b>2</b> 0	mA
l <sub>out</sub>	DC Output Current, per Pin	±[ <b>2</b> 5	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±[ <b>5</b> 0	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{\rm CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	٧
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	٧
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0	1000 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

		Test Conditions		Gu	aranteed Li	mit	
Symbol	Parameter		v <sub>cc</sub> v	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V	2.0	1.5	1.5	1.5	V
	Voltage	$ I_{out}  \le 20 \mu A$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low-Level Input	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	2.0	0.5	0.5	0.5	V
	Voltage	$ I_{out}  \leq 20 \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out}  \leq 20 \mu A$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH} \text{ or } V_{IL}   I_{out}  \leq 2.4 \text{ mA}$	3.0	2.48	2.34	2.20	
		$ I_{\text{out}}  \leq 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out}  \le 5.2 \text{ mA}$	6.0	5.48	5.34	5.2	
V <sub>OL</sub>	Maximum Low-Level Output	$V_{in} = V_{IH}$ or $V_{IL}$	2.0	0.1	0.1	0.1	V
	Voltage	$ I_{out}  \leq 20 \mu A$	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL}   I_{out}  \leq 2.4 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out}  \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out}  \leq 5.2 \text{mA}$	6.0	0.26	0.33	0.4	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±[0.1	±]1.0	± <u>1</u> 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND  I <sub>out</sub>   = 0 μA	6.0	1.0	10	40	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Gate)*	22	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MC74HC02AN	PDIP-14		
MC74HC02ANG	PDIP-14 (Pb-Free)	25 Units/Rail	
MC74HC02AD	SOIC-14		
MC74HC02ADG	SOIC-14 (Pb-Free)	55 Units / Rail	
MC74HC02ADR2	SOIC-14		
MC74HC02ADR2G	SOIC-14 (Pb-Free)	2500/Tape & Reel	
MC74HC02ADTR2	TSSOP-14*	·	
MC74HC02ADTR2G	TSSOP-14*		
MC74HC02AFEL	SOEIAJ-14		
MC74HC02AFELG	SOEIAJ-14 (Pb-Free)	2000/Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb–Free.

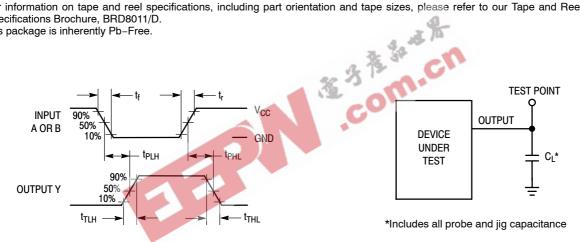
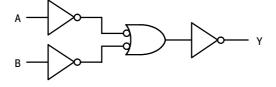


Figure 1. Switching Waveforms

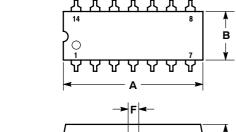
Figure 2. Test Circuit

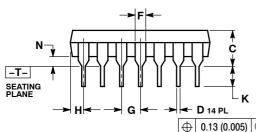
# **EXPANDED LOGIC DIAGRAM** (1/4 OF THE DEVICE)

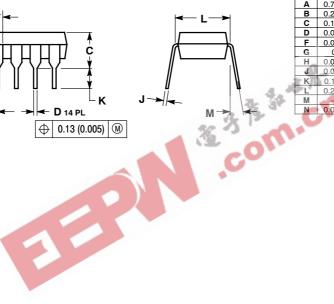


# **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 ISSUE P





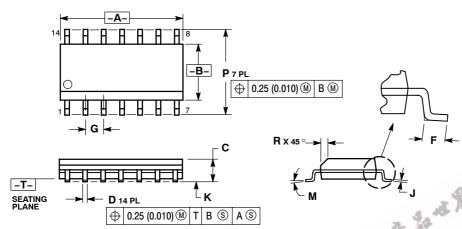


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54 BSC	
H	0.052	0.095	1.32	2.41
d	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L.	0.290	0.310	7.37	7.87
M	-	10 °		10 °
N	0.015	0.039	0.38	1.01

# **PACKAGE DIMENSIONS**

SOIC-14 CASE 751A-03 **ISSUE H** 

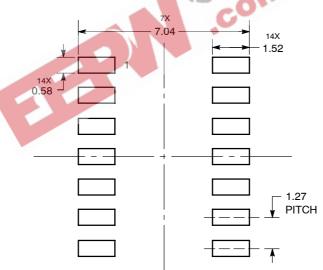


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

- I. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
O	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
C	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# SOLDERING FOOTPRINT

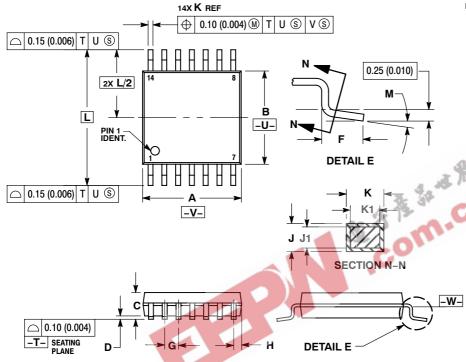


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# PACKAGE DIMENSIONS

# TSSOP-14 CASE 948G-01 **ISSUE B**

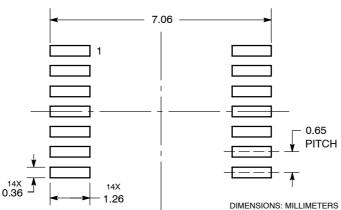


- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  - INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W—.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
c		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252 BSC	
М	0 °	8 °	0 °	8 °

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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